

Amendments to the Claims:

Please amend claims 4, 76, 81 as follows:

Listing of Claims:

1-3. (Cancelled)

GT
~~4.~~ (Currently Amended) A method of passivating a conductive material, comprising:

providing said conductive material, wherein said conductive material has an ability to associate with oxygen; and
exposing said conductive material to a ~~material selected from the group consisting of phosphine, and methylsilane.~~

[
5-75. (Cancelled)

~~76.~~ (Currently Amended) A method of passivating a conductive layer, comprising:

providing a tungsten nitride layer;
providing a polysilicon layer on the tungsten nitride layer; and
exposing the tungsten nitride layer to a ~~material selected from the group consisting of phosphine, and methylsilane.~~

~~77.~~ (Previously Presented) The method in claim ~~76~~⁵, wherein exposing the tungsten nitride layer comprises exposing the tungsten nitride layer to at least one material in the recited group under process conditions comprising:

a flow rate of the material of about 2 sccm to about 400 sccm;
a flow rate of about 50 sccm to about 100 sccm for an inert carrier gas;
a temperature ranging from about 150 to about 600 degrees Celsius;
a pressure ranging from about 50 millitorr to about 760 torr; and

a process time ranging from about 50 to about 500 seconds.

78-80. (Cancelled)

⁸
~~81.~~ (Currently Amended) A method of passivating a conductive layer, comprising:

providing a first conductive plug;

providing a first conductive layer on the plug;

exposing the first conductive layer to ~~a material selected from the group consisting of phosphine, and methylsilane; and~~

after exposing the first conductive layer, forming a second conductive layer on the first conductive layer.

⁹
~~82.~~ (Previously Presented) The method of claim ⁸~~81~~ wherein the plug comprises at least one of polysilicon, tungsten, copper, and aluminum.

¹⁰
~~83.~~ (Previously Presented) The method of claim ⁸~~81~~ wherein the first conductive layer comprises tungsten nitride.

¹¹
~~84.~~ (Previously Presented) The method of claim ⁸~~81~~ wherein the second conductive layer comprises copper.

¹²
~~85.~~ (Previously Presented) The method of claim ⁸~~81~~ wherein exposing the first conductive layer reduces an ability of the first conductive layer to associate with oxygen.

86-88. (Cancelled)

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~~89~~

(Previously Presented) The method of claim ~~4~~¹ wherein the conductive layer comprises at least one of tungsten nitride, polysilicon, tungsten, copper, and aluminum.

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~~90~~

(Previously Presented) The method of claim ~~4~~¹ wherein exposing said conductive material comprises exposing the conductive material to at least one material in the recited group under process conditions comprising:

- a flow rate of the material of about 2 sccm to about 400 sccm;
- a flow rate of about 50 sccm to about 100 sccm for an inert carrier gas;
- a temperature ranging from about 150 to about 600 degrees Celsius;
- a pressure ranging from about 50 millitorr to about 760 torr; and
- a process time ranging from about 50 to about 500 seconds.

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~~91~~

(Previously Presented) The method of claim ~~90~~³ wherein the inert carrier gas comprises He or Ar.

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~~92~~

(Previously Presented) The method of claim ~~71~~⁶ wherein the inert carrier gas comprises He or Ar.

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